## **LPC662**

LPC662 Low Power CMOS Dual Operational Amplifier



Literature Number: SNOS555B



### **LPC662**

## Low Power CMOS Dual Operational Amplifier

### **General Description**

The LPC662 CMOS Dual operational amplifier is ideal for operation from a single supply. It features a wide range of operating voltage from +5V to +15V, rail-to-rail output swing in addition to an input common-mode range that includes ground. Performance limitations that have plagued CMOS amplifiers in the past are not a problem with this design. Input  $V_{\rm OS},$  drift, and broadband noise as well as voltage gain (into 100 k $\Omega$  and 5 k $\Omega$ ) are all equal to or better than widely accepted bipolar equivalents, while the power supply requirement is typically less than 0.5 mW.

This chip is built with National's advanced Double-Poly Silicon-Gate CMOS process.

See the LPC660 datasheet for a Quad CMOS operational amplifier and LPC661 for a single CMOS operational amplifier with these same features.

### **Applications**

- High-impedance buffer
- Precision current-to-voltage converter

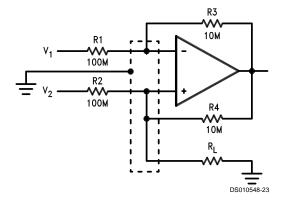
- Long-term integrator
- High-impedance preamplifier
- Active filter
- Sample-and-Hold circuit
- Peak detector

### **Features**

- Rail-to-rail output swing
- Micropower operation (<0.5 mW)
- Specified for 100 kΩ and 5 kΩ loads
- High voltage gain■ Low input offset voltage120 dB3 mV
- Low offset voltage drift 1.3 µV/°C
   Ultra low input bias current 2 fA
- Input common-mode includes GND
- Operating range from +5V to +15V
- Low distortion 0.01% at 1 kHz
- Slew rate 0.11 V/µs
- Full military temperature range available

### **Application Circuit**

#### **Howland Current Pump**



### **Absolute Maximum Ratings** (Note 3)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Differential Input Voltage ±Supply Voltage Supply Voltage (V<sup>+</sup> – V<sup>-</sup>) 16V Output Short Circuit to V+ (Note 11) Output Short Circuit to V-(Note 1) Lead Temperature (Soldering, 10 sec.) 260°C Storage Temp. Range -65°C to +150°C Junction Temperature 150°C **ESD** Rating

 $\begin{array}{ll} \text{(C = 100 pF, R = 1.5 k}\Omega) & 1000\text{V} \\ \text{Power Dissipation} & \text{(Note 2)} \\ \text{Current at Input Pin} & \pm 5 \text{ mA} \\ \text{Current at Output Pin} & \pm 18 \text{ mA} \\ \end{array}$ 

Current at Power Supply Pin 35 mA Voltage at Input/Output Pin  $(V^+) + 0.3V$ ,  $(V^-) -0.3V$ 

### **Operating Ratings** (Note 3)

Temperature Range

Thermal Resistance ( $\theta_{JA}$ ) (Note 10)

 8-Pin Ceramic DIP
 100°C/W

 8-Pin Molded DIP
 101°C/W

 8-Pin SO
 165°C/W

 8-Pin Side Brazed Ceramic DIP
 100°C/W

### **DC Electrical Characteristics**

Unless otherwise specified, all limits guaranteed for  $T_J = 25^{\circ}C$ . **Boldface** limits apply at the temperature extremes.  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 1.5V$ ,  $V_O = 2.5V$  and  $R_L > 1M$  unless otherwise specified.

			LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
			Limit	(Note 4)	(Note 4)	
			(Notes 4, 8)			
Input Offset Voltage		1	3	3	6	mV
			3.5	3.3	6.3	max
Input Offset Voltage		1.3				μV/°C
Average Drift						
Input Bias Current		0.002	20			pА
			100	4	4	max
Input Offset Current		0.001	20			pА
			100	2	2	max
Input Resistance		>1				Tera Ω
Common Mode	$0V \le V_{CM} \le 12.0V$	83	70	70	63	dB
Rejection Ratio	V+ = 15V		68	68	61	min
Positive Power Supply	5V ≤ V <sup>+</sup> ≤ 15V	83	70	70	63	dB
Rejection Ratio	$V_{O} = 2.5V$		68	68	61	min
Negative Power Supply	0V ≤ V <sup>-</sup> ≤ <b>-</b> 10V	94	84	84	74	dB
Rejection Ratio			82	83	73	min
Input Common-Mode	V <sup>+</sup> = 5V and 15V	-0.4	-0.1	-0.1	-0.1	V
Voltage Range	For CMRR ≥ 50 dB		0	0	0	max
		V <sup>+</sup> – 1.9	V <sup>+</sup> - 2.3	V <sup>+</sup> - 2.3	V <sup>+</sup> - 2.3	V
			V+ - 2.6	V+ - 2.5	V+ - 2.5	min
Large Signal	$R_L = 100 \text{ k}\Omega \text{ (Note 5)}$	1000	400	400	300	V/mV
Voltage Gain	Sourcing		250	300	200	min
	Sinking	500	180	180	90	V/mV
			70	120	70	min
	$R_L = 5 \text{ k}\Omega \text{ (Note 5)}$	1000	200	200	100	V/mV
	Sourcing		150	160	80	min
	Sinking	250	100	100	50	V/mV
			35	60	40	min

### DC Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for  $T_J = 25^{\circ}C$ . **Boldface** limits apply at the temperature extremes.  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 1.5V$ ,  $V_O = 2.5V$  and  $R_L > 1M$  unless otherwise specified.

		<u> </u>	LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
T didiliotoi	Conditions	.,,,,	Limit	(Note 4)	(Note 4)	00
			(Notes 4, 8)	(11010-1)	(11010-1)	
Output Swing	V <sup>+</sup> = 5V	4.987	4.970	4.970	4.940	V
	$R_{L} = 100 \text{ k}\Omega \text{ to V}^{+}/2$		4.950	4.950	4.910	min
		0.004	0.030	0.030	0.060	V
			0.050	0.050	0.090	max
	V <sup>+</sup> = 5V	4.940	4.850	4.850	4.750	V
	$R_L = 5 \text{ k}\Omega \text{ to V}^+/2$		4.750	4.750	4.650	min
		0.040	0.150	0.150	0.250	V
			0.250	0.250	0.350	max
	V <sup>+</sup> = 15V	14.970	14.920	14.920	14.880	V
	$R_{L} = 100 \text{ k}\Omega \text{ to V}^{+}/2$		14.880	14.880	14.820	min
		0.007	0.030	0.030	0.060	V
			0.050	0.050	0.090	max
	V <sup>+</sup> = 15V	14.840	14.680	14.680	14.580	V
	$R_L = 5 \text{ k}\Omega \text{ to V}^+/2$		14.600	14.600	14.480	min
		0.110	0.220	0.220	0.320	V
			0.300	0.300	0.400	max
Output Current	Sourcing, V <sub>O</sub> = 0V	22	16	16	13	mA
$V^{+} = 5V$			12	14	11	min
	Sinking, $V_O = 5V$	21	16	16	13	mA
			12	14	11	min
Output Current	Sourcing, V <sub>O</sub> = 0V	40	19	28	23	mA
$V^{+} = 15V$			19	25	20	min
	Sinking, V <sub>O</sub> = 13V	39	19	28	23	mA
	(Note 11)		19	24	19	min
Supply Current	Both Amplifiers	86	120	120	140	μA
	V <sub>O</sub> = 1.5V		145	140	160	max

### **AC Electrical Characteristics**

Unless otherwise specified, all limits guaranteed for  $T_J = 25^{\circ}C$ . **Boldface** limits apply at the temperature extremes.  $V^+ = 5V$ ,  $V^- = 0V$ ,  $V_{CM} = 1.5V$ ,  $V_O = 2.5V$  and  $R_L > 1M$  unless otherwise specified.

			LPC662AM	LPC662AI	LPC662I	
Parameter	Conditions	Тур	LPC662AMJ/883	Limit	Limit	Units
			Limit	(Note 4)	(Note 4)	
			(Notes 4, 8)			
Slew Rate	(Note 6)	0.11	0.07	0.07	0.05	V/µs
			0.04	0.05	0.03	min
Gain-Bandwidth Product		0.35				MHz
Phase Margin		50				Deg
Gain Margin		17				dB
Amp-to-Amp Isolation	(Note 7)	130				dB
Input Referred Voltage Noise	F = 1 kHz	42				nV/√ <del>Hz</del>
Input Referred Current Noise	F = 1 kHz	0.0002				pA/√Hz
Total Harmonic Distortion	$F = 1 \text{ kHz}, A_V = -10, V^+ = 15V$	0.01				%
	$R_L = 100 \text{ k}\Omega, V_O = 8 V_{PP}$					

Note 1: Applies to both single supply and split supply operation. Continuous short circuit operation at elevated ambient temperature and/or multiple Op Amp shorts can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.

Note 2: The maximum power dissipation is a function of  $T_{J(max)}$ ,  $\theta_{JA}$ , and  $T_A$ . The maximum allowable power dissipation of any ambient temperature is  $P_D = (T_{J(max)} - T_A)/\theta_{JA}$ .

**Note 3:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

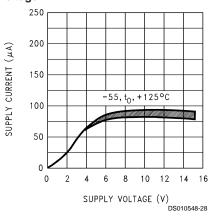
- Note 4: Limits are guaranteed by testing or correlation.
- Note 5:  $V^+ = 15V$ ,  $V_{CM} = 7.5V$  and  $R_L$  connected to 7.5V. For Sourcing tests,  $7.5V \le V_O \le 11.5V$ . For Sinking tests,  $2.5V \le V_O \le 7.5V$ .
- Note 6: V<sup>+</sup> = 15V. Connected as Voltage Follower with 10V step input. Number specified is the slower of the positive and negative slew rates.
- Note 7: Input referred.  $V^+ = 15V$  and  $R_L = 100 \text{ k}\Omega$  connected to  $V^+/2$ . Each amp excited in turn with 1 kHz to produce  $V_O = 13 \text{ V}_{PP}$ .

Note 8: A military RETS electrical test specification is available on request. At the time of printing, the LPC662AMJ/883 RETS specification complied fully with the boldface limits in this column. The LPC662AMJ/883 may also be procured to a Standard Military Drawing specification.

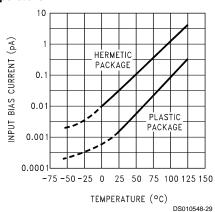
- Note 9: For operating at elevated temperatures the device must be derated based on the thermal resistance  $\theta_{JA}$  with  $P_D = (T_J T_A)/\theta_{JA}$ .
- Note 10: All numbers apply for packages soldered directly into a PC board.
- Note 11: Do not connect output to V+when V+ is greater than 13V or reliability may be adversely affected.

# Typical Performance Characteristics $V_S = \pm 7.5 V$ , $T_A = 25^{\circ} C$ unless otherwise specified

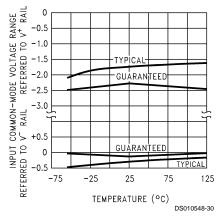
### Supply Current vs Supply Voltage



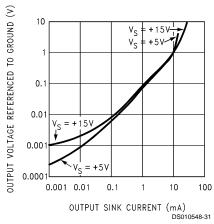
# Input Bias Current vs Temperature



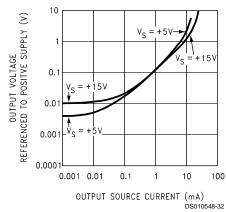
### Input Common-Mode Voltage Range vs Temperature



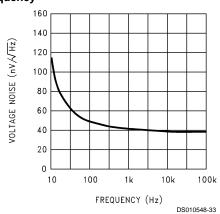
# Output Characteristics Current Sinking



### Output Characteristics Current Sourcing

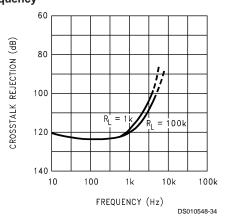


# Input Voltage Noise vs Frequency

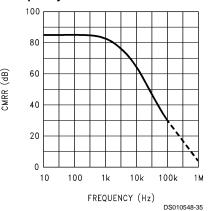


# Typical Performance Characteristics $V_S = \pm 7.5 \text{V}$ , $T_A = 25^{\circ}\text{C}$ unless otherwise specified (Continued)

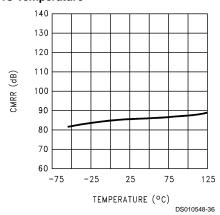
# Crosstalk Rejection vs Frequency



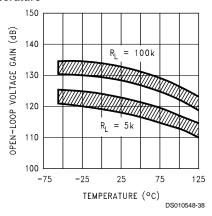
### **CMRR** vs Frequency



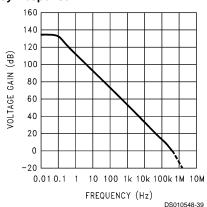
### **CMRR** vs Temperature



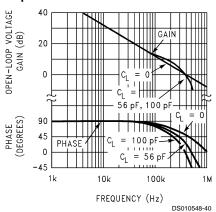
# Open-Loop Voltage Gain vs Temperature



#### Open-Loop Frequency Response

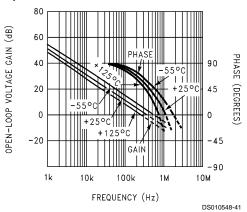


# Gain and Phase Responses vs Load Capacitance

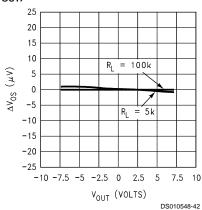


## $\textbf{Typical Performance Characteristics} \ \ V_{\text{S}} = \pm 7.5 \text{V}, \ T_{\text{A}} = 25 ^{\circ} \text{C unless otherwise specified (Continued)}$

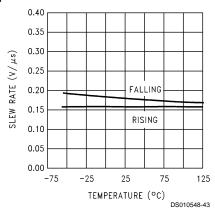
# Gain and Phase Responses vs Temperature



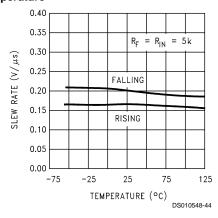
### Gain Error (V<sub>OS</sub>vs V<sub>OUT</sub>)



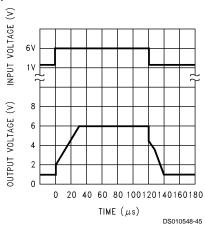
# Non-Inverting Slew Rate vs Temperature



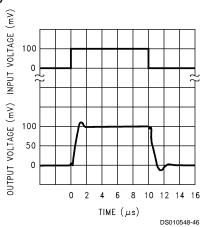
# Inverting Slew Rate vs Temperature



#### Large-Signal Pulse Non-Inverting Response (A<sub>V</sub> = +1)

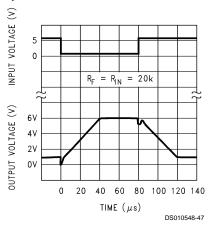


### Non-Inverting Small Signal Pulse Response $(A_V = +1)$

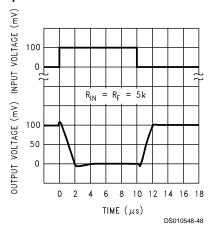


# Typical Performance Characteristics $V_S = \pm 7.5 \text{V}$ , $T_A = 25^{\circ}\text{C}$ unless otherwise specified (Continued)

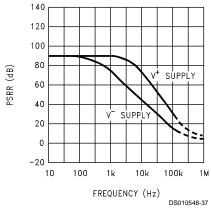
# Inverting Large-Signal Pulse Response



# Inverting Small-Signal Pulse Response

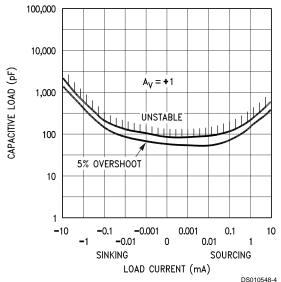


### Power Supply Rejection Ratio vs Frequency



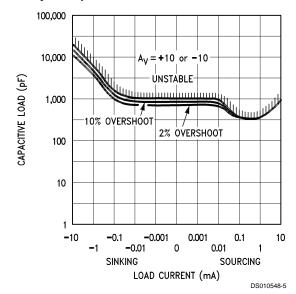
## 140 140

## Stability vs Capacitive Load



### Note: Avoid resistive loads of less than $500\Omega,$ as they may cause instability.

#### Stability vs Capacitive Load



### **Application Hints**

#### **AMPLIFIER TOPOLOGY**

The topology chosen for the LPC662 is unconventional (compared to general-purpose op amps) in that the traditional unity-gain buffer output stage is not used; instead, the output is taken directly from the output of the integrator, to allow rail-to-rail output swing. Since the buffer traditionally delivers the power to the load, while maintaining high op amp gain and stability, and must withstand shorts to either rail, these tasks now fall to the integrator.

As a result of these demands, the integrator is a compound affair with an embedded gain stage that is doubly fed forward (via  $C_{\rm f}$  and  $C_{\rm ff}$ ) by a dedicated unity-gain compensation driver. In addition, the output portion of the integrator is a push-pull configuration for delivering heavy loads. While sinking current the whole amplifier path consists of three gain stages with one stage fed forward, whereas while sourcing the path contains four gain stages with two fed forward

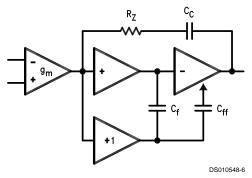


FIGURE 1. LPC662 Circuit Topology (Each Amplifier)

The large signal voltage gain while sourcing is comparable to traditional bipolar op amps for load resistance of at least 5 k $\Omega$ . The gain while sinking is higher than most CMOS op amps, due to the additional gain stage; however, when driving load resistance of 5 k $\Omega$  or less, the gain will be reduced as indicated in the Electrical Characteristics. The op amp can drive load resistance as low as 500 $\Omega$  without instability.

#### **COMPENSATING INPUT CAPACITANCE**

Refer to the LMC660 or LMC662 datasheets to determine whether or not a feedback capacitor will be necessary for compensation and what the value of that capacitor would be.

#### **CAPACITIVE LOAD TOLERANCE**

Like many other op amps, the LPC662 may oscillate when its applied load appears capacitive. The threshold of oscillation varies both with load and circuit gain. The configuration most sensitive to oscillation is a unity-gain follower. See the Typical Performance Characteristics.

The load capacitance interacts with the op amp's output resistance to create an additional pole. If this pole frequency is sufficiently low, it will degrade the op amp's phase margin so that the amplifier is no longer stable at low gains. The addition of a small resistor ( $50\Omega$  to  $100\Omega$ ) in series with the op amp's output, and a capacitor (5 pF to 10 pF) from inverting input to output pins, returns the phase margin to a safe value without interfering with lower-frequency circuit operation. Thus, larger values of capacitance can be

tolerated without oscillation. Note that in all cases, the output will ring heavily when the load capacitance is near the threshold for oscillation.

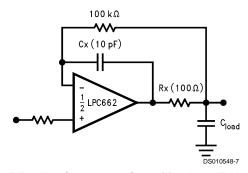


FIGURE 2. Rx, Cx Improve Capacitive Load Tolerance

Capacitive load driving capability is enhanced by using a pull up resistor to V\* Figure 3. Typically a pull up resistor conducting 50  $\,\mu\text{A}$  or more will significantly improve capacitive load responses. The value of the pull up resistor must be determined based on the current sinking capability of the amplifier with respect to the desired output swing. Open loop gain of the amplifier can also be affected by the pull up resistor (see Electrical Characteristics).

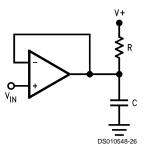


FIGURE 3. Compensating for Large Capacitive Loads with A Pull Up Resistor

# PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the LPC662, typically less than 0.04 pA, it is essential to have an excellent layout. Fortunately, the techniques for obtaining low leakages are quite simple. First, the user must not ignore the surface leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the LPC662's inputs and the terminals of capacitors, diodes, conductors, resistors, relay terminals, etc. connected to the op-amp's inputs. See *Figure 4*. To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of 10<sup>12</sup> ohms, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of an input.

### **Application Hints** (Continued)

This would cause a 100 times degradation from the LPC662's actual performance. However, if a guard ring is held within 5 mV of the inputs, then even a resistance of 10<sup>11</sup> ohms would cause only 0.05 pA of leakage current, or perhaps a minor (2:1) degradation of the amplifier's

performance. See *Figure 5a*, *Figure 5b*, *Figure 5c* for typical connections of guard rings for standard op-amp configurations. If both inputs are active and at high impedance, the guard can be tied to ground and still provide some protection; see *Figure 5d*.

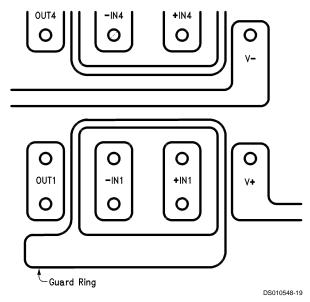
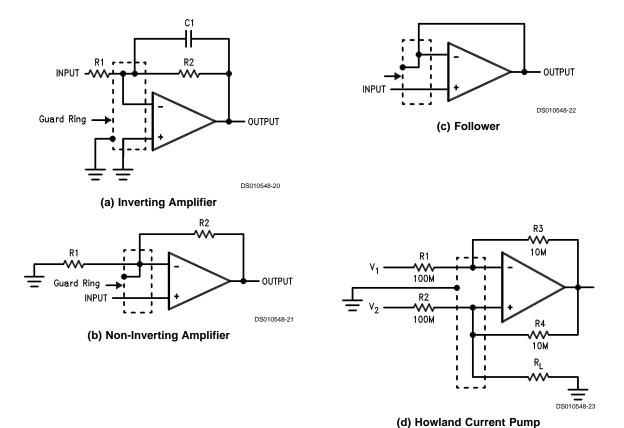


FIGURE 4. Example of Guard Ring in P.C. Board Layout, using the LPC660



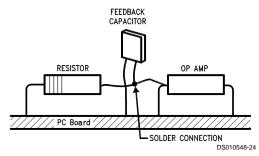
**FIGURE 5. Guard Ring Connections** 

The designer should be aware that when it is inappropriate to lay out a PC board for the sake of just a few circuits, there

is another technique which is even better than a guard ring on a PC board: Don't insert the amplifier's input pin into the

### **Application Hints** (Continued)

board at all, but bend it up in the air and use only air as an insulator. Air is an excellent insulator. In this case you may have to forego some of the advantages of PC board construction, but the advantages are sometimes well worth the effort of using point-to-point up-in-the-air wiring. See *Figure 6*.



(Input pins are lifted out of PC board and soldered directly to components. All other pins connected to PC board.)

### FIGURE 6. Air Wiring

#### **BIAS CURRENT TESTING**

The test method of *Figure 7* is appropriate for bench-testing bias current with reasonable accuracy. To understand its operation, first close switch S2 momentarily. When S2 is opened, then

$$I^{-} = \frac{dV_{OUT}}{dt} \times C2.$$

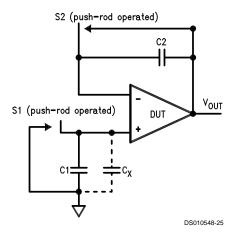


FIGURE 7. Simple Input Bias Current Test Circuit

A suitable capacitor for C2 would be a 5 pF or 10 pF silver mica, NPO ceramic, or air-dielectric. When determining the magnitude of  $I^-$ , the leakage of the capacitor and socket must be taken into account. Switch S2 should be left shorted most of the time, or else the dielectric absorption of the capacitor C2 could cause errors.

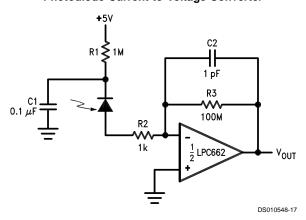
Similarly, if S1 is shorted momentarily (while leaving S2 shorted)  $\,$ 

$$I^{+} = \frac{dV_{OUT}}{dt} \times (C1 + C_{x})$$

where C<sub>x</sub> is the stray capacitance at the + input.

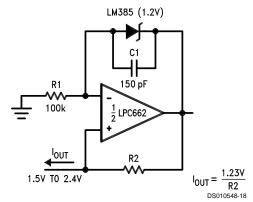
### **Typical Single-Supply Applications** $(V^+ = 5.0 V_{DC})$

#### Photodiode Current-to-Voltage Converter



**Note:** A 5V bias on the photodiode can cut its capacitance by a factor of 2 or 3, leading to improved response and lower noise. However, this bias on the photodiode will cause photodiode leakage (also known as its dark current).

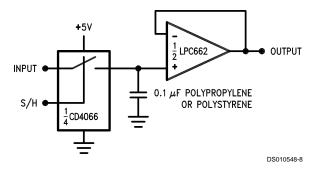
#### **Micropower Current Source**



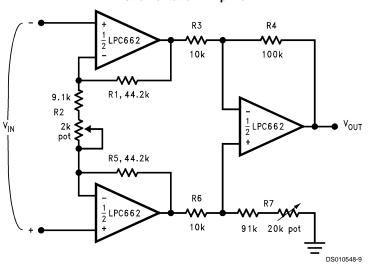
**Note:** (Upper limit of output range dictated by input common-mode range; lower limit dictated by minimum current requirement of LM385.)

## Typical Single-Supply Applications ( $V^+ = 5.0 V_{DC}$ ) (Continued)

#### Low-Leakage Sample-and-Hold



### **Instrumentation Amplifier**



If R1 = R5, R3 = R6 and R4 = R7; then

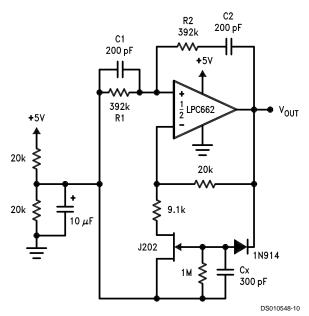
$$\frac{V_{OUT}}{V_{IN}} = \frac{R2\,+\,2R1}{R2} \times \frac{R4}{R3}$$

 $\therefore A_V \approx 100$  for circuit shown.

For good CMRR over temperature, low drift resistors should be used. Matching of R3 to R6 and R4 to R7 affects CMRR. Gain may be adjusted through R2. CMRR may be adjusted through R7.

## **Typical Single-Supply Applications** $(V^+ = 5.0 V_{DC})$ (Continued)

#### **Sine-Wave Oscillator**



Oscillator frequency is determined by R1, R2, C1, and C2:

 $f_{OSC} = 1/2\pi RC$ 

where R = R1 = R2 and C = C1 = C2.

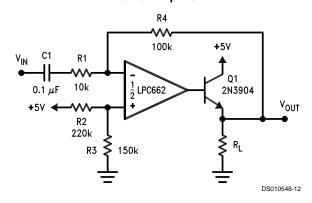
This circuit, as shown, oscillates at 2.0 kHz with a peak-to-peak output swing of 4.5V

DS010548-11

### 1 Hz Square-Wave Oscillator

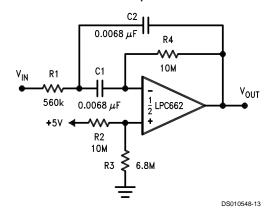
# 

### **Power Amplifier**



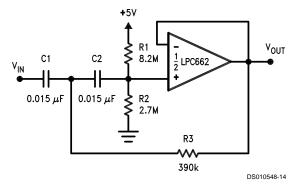
### Typical Single-Supply Applications (V<sup>+</sup> = 5.0 V<sub>DC</sub>) (Continued)

#### 10 Hz Bandpass Filter



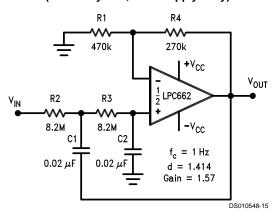
 $f_{O} = 10 \text{ Hz}$  Q = 2.1Gain = -8.8

### 10 Hz High-Pass Filter (2 dB Dip)

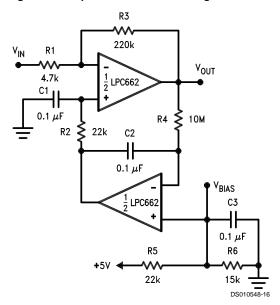


 $f_c = 10 \text{ Hz}$  d = 0.895Gain = 1

# 1 Hz Low-Pass Filter (Maximally Flat, Dual Supply Only)

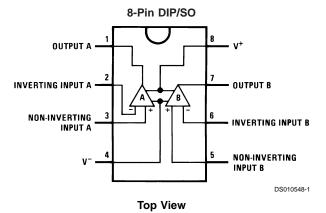


#### High Gain Amplifier with Offset Voltage Reduction



 $\label{eq:Gain} \mbox{Gain} = -46.8$  Output offset voltage reduced to the level of the input offset voltage of the bottom amplifier (typically 1 mV), referred to  $\mbox{V}_{\mbox{BIAS}}.$ 

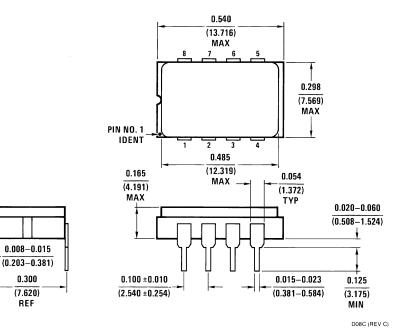
## **Connection Diagram**



# **Ordering Information**

Package	Temperatu	re Range	NSC	Transport
	Military	Industrial	Drawing	Media
8-Pin	LPC662AMD		D08C	Rail
Side Brazed				
Ceramic DIP				
8-Pin		LPC662AIM	M08A	Rail
Small Outline		or LPC662IM		Tape and Reel
8-Pin		LPC662AIN	N08E	Rail
Molded DIP		or LPC662IN		
8-Pin	LPC662AMJ/883		J08A	Rail
Ceramic DIP				

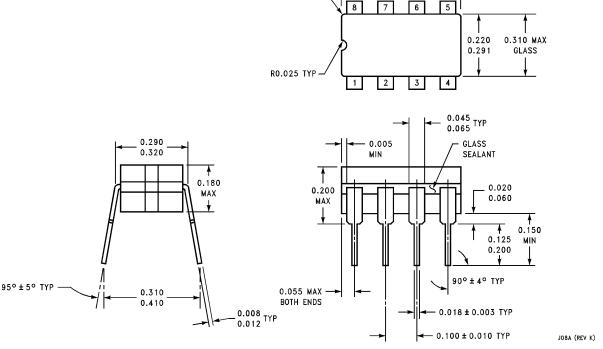
### Physical Dimensions inches (millimeters) unless otherwise noted



8-Pin Cavity Dual-In-Line Package (D) Order Number LPC662AMD NS Package Number D08C

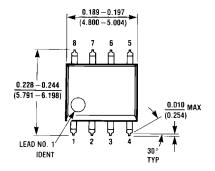
R0.010 TYP

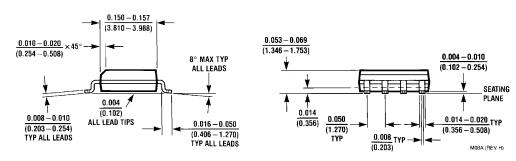
0.400 MAX



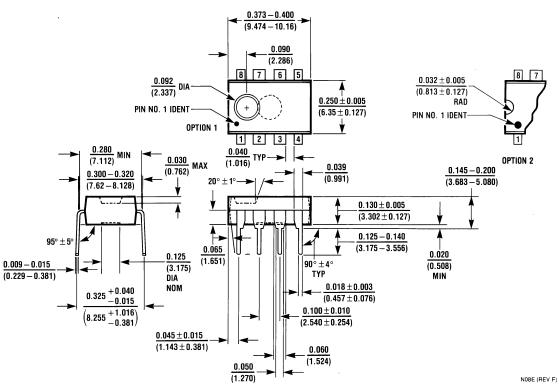
Ceramic Dual-In-Line Package (J) Order Number LPC662AMJ/883 NS Package Number J08A

### Physical Dimensions inches (millimeters) unless otherwise noted (Continued)





8-Pin Small Outline Molded Package (M)
Order Number LPC662AIM or LPC662IM
NS Package Number M08A



8-Pin Molded Dual-In-Line Package (N) Order Number LPC662AIN or LPC662IN NS Package Number N08E

### **Notes**

#### LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



**National Semiconductor** Corporation Americas

Tel: 1-800-272-9959 Fax: 1-800-737-7018 Email: support@nsc.com www.national.com

**National Semiconductor** Europe

Fax: +49 (0) 180-530 85 86 Email: europe.support@nsc.com Deutsch Tel: +49 (0) 69 9508 6208 English Tel: +44 (0) 870 24 0 2171 Français Tel: +33 (0) 1 41 91 8790

**National Semiconductor** Asia Pacific Customer Response Group Tel: 65-2544466

Fax: 65-2504466 Email: ap.support@nsc.com **National Semiconductor** Tel: 81-3-5639-7560 Fax: 81-3-5639-7507

www.ti.com

11-Nov-2025

### **PACKAGING INFORMATION**

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
LPC662AIM/NOPB	Active	Production	SOIC (D)   8	95   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2AIM
LPC662AIM/NOPB.A	Active	Production	SOIC (D)   8	95   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2AIM
LPC662AIM/NOPB.B	Active	Production	SOIC (D)   8	95   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2AIM
LPC662AIMX/NOPB	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2AIM
LPC662AIMX/NOPB.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2AIM
LPC662AIMX/NOPB.B	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2AIM
LPC662IM/NOPB	Active	Production	SOIC (D)   8	95   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2IM
LPC662IM/NOPB.A	Active	Production	SOIC (D)   8	95   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2IM
LPC662IM/NOPB.B	Active	Production	SOIC (D)   8	95   TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2IM
LPC662IMX/NOPB	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2IM
LPC662IMX/NOPB.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2IM
LPC662IMX/NOPB.B	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LPC66 2IM

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.



### **PACKAGE OPTION ADDENDUM**

www.ti.com 11-Nov-2025

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

### **PACKAGE MATERIALS INFORMATION**

www.ti.com 25-Aug-2025

### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LPC662AIMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LPC662IMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1

### **PACKAGE MATERIALS INFORMATION**

www.ti.com 25-Aug-2025



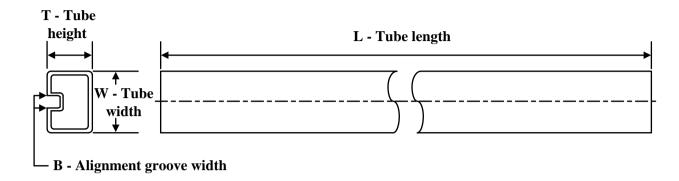
### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LPC662AIMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LPC662IMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0

### **PACKAGE MATERIALS INFORMATION**

www.ti.com 25-Aug-2025

### **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
LPC662AIM/NOPB	D	SOIC	8	95	495	8	4064	3.05
LPC662AIM/NOPB.A	D	SOIC	8	95	495	8	4064	3.05
LPC662AIM/NOPB.B	D	SOIC	8	95	495	8	4064	3.05
LPC662IM/NOPB	D	SOIC	8	95	495	8	4064	3.05
LPC662IM/NOPB.A	D	SOIC	8	95	495	8	4064	3.05
LPC662IM/NOPB.B	D	SOIC	8	95	495	8	4064	3.05

### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025